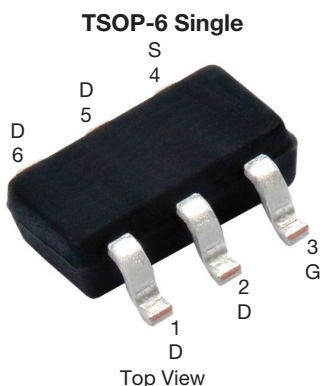


# N-Channel 150 V (D-S) MOSFET



## FEATURES

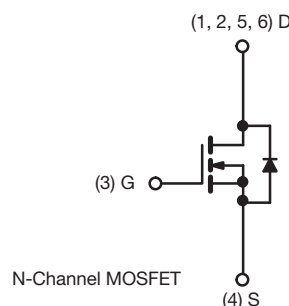
- TrenchFET® power MOSFET
- PWM optimized for fast switching in small footprint
- 100 % R<sub>g</sub> tested
- Material categorization:  
for definitions of compliance please see  
[www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

## APPLICATIONS

- Primary side switch for low power DC/DC converters



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	150
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 10 V	0.375
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 6 V	0.400
Q <sub>g</sub> typ. (nC)	5.4
I <sub>D</sub> (A)	1.5
Configuration	Single

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free	Si3440DV-T1-E3
Lead (Pb)-free and halogen-free	Si3440DV-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V <sub>DS</sub>	150	V	
Gate-source voltage	V <sub>GS</sub>	± 20	V	
Continuous drain current (T <sub>J</sub> = 175 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	1.2	A	
	T <sub>A</sub> = 85 °C	0.8		
Pulsed drain current	I <sub>DM</sub>	6		
Single avalanche current	I <sub>AS</sub>	4		
Single avalanche energy (duty cycle ≤ 1 %)	E <sub>AS</sub>	0.8	mJ	
Continuous source current (diode conduction) <sup>a</sup>	I <sub>S</sub>	1	A	
Maximum power dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	1.14	W	
	T <sub>A</sub> = 85 °C	0.59		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient <sup>a</sup>	R <sub>thJA</sub>	45	62.5	°C/W	
		90	110		
Maximum junction-to-foot (drain)	R <sub>thJF</sub>	25	30		

## Notes

a. Surface mounted on 1" x 1" FR4 board



SPECIFICATIONS ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	-	4	V
Gate-body leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 150\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 150\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 85\text{ }^{\circ}\text{C}$	-	-	5	
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$ , $V_{GS} = 10\text{ V}$	4	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 1.5\text{ A}$	-	0.310	0.375	$\Omega$
		$V_{GS} = 6\text{ V}$ , $I_D = 1.4\text{ A}$	-	0.330	0.400	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 1.5\text{ A}$	-	4.1	-	S
Diode forward voltage <sup>a</sup>	$V_{SD}$	$I_S = 1.7\text{ A}$ , $V_{GS} = 0\text{ V}$	-	0.8	1.2	V
<b>Dynamic <sup>b</sup></b>						
Total gate charge	$Q_g$	$V_{DS} = 75\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 1.5\text{ A}$	-	5.4	8	nC
Gate-source charge	$Q_{gs}$		-	1.1	-	
Gate-drain charge	$Q_{gd}$		-	1.9	-	
Gate resistance	$R_g$	$f = 1\text{ MHz}$	4	9	15	$\Omega$
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 75\text{ V}$ , $R_L = 75\text{ }\Omega$ $I_D \cong 1\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 6\text{ }\Omega$	-	8	15	ns
Rise time	$t_r$		-	10	15	
Turn-off delay time	$t_{d(off)}$		-	20	30	
Fall time	$t_f$		-	15	25	
Source-drain reverse recovery time	$t_{rr}$	$I_F = 1.7\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}$	-	40	60	

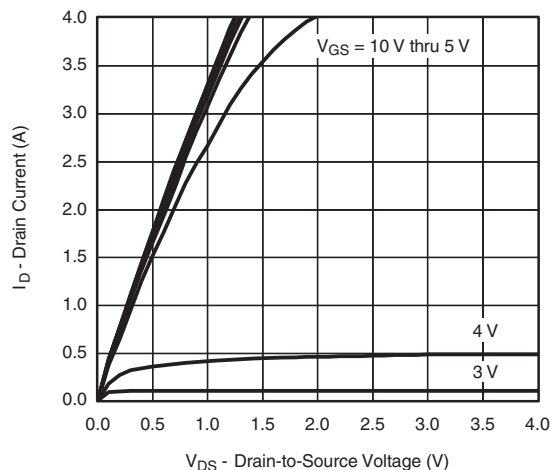
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

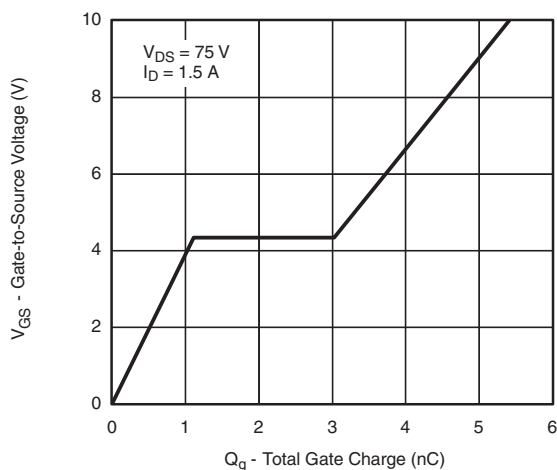
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



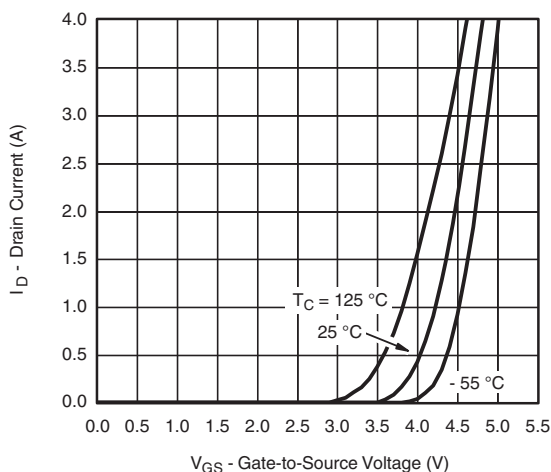
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



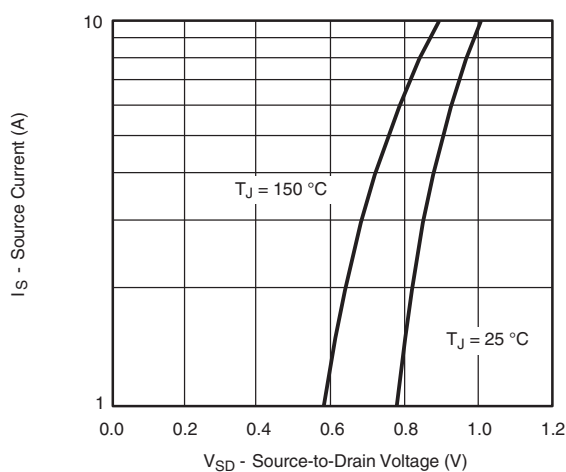
**Output Characteristics**



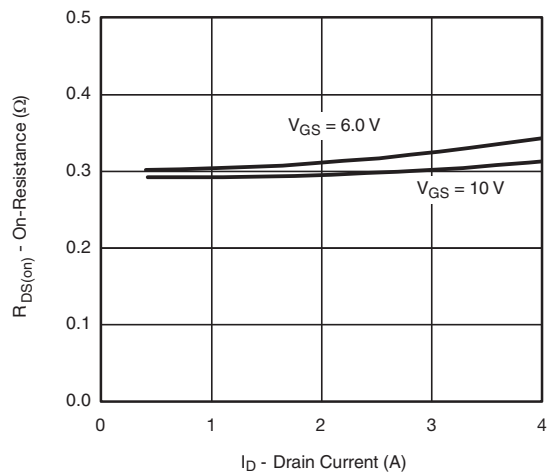
**Gate Charge**



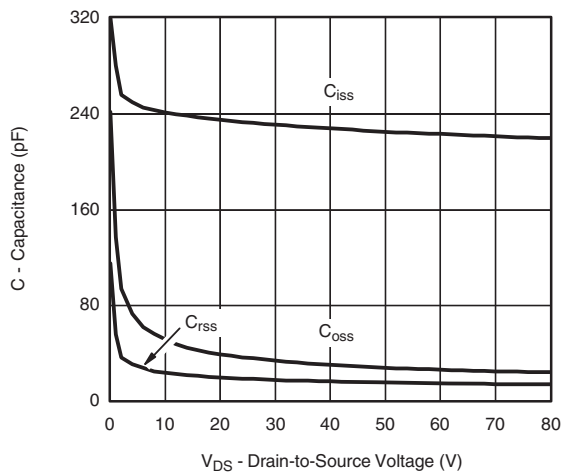
**Transfer Characteristics**



**Source-Drain Diode Forward Voltage**



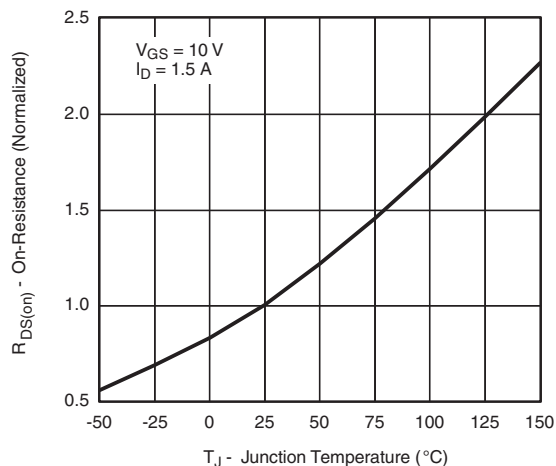
**On-Resistance vs. Drain Current**



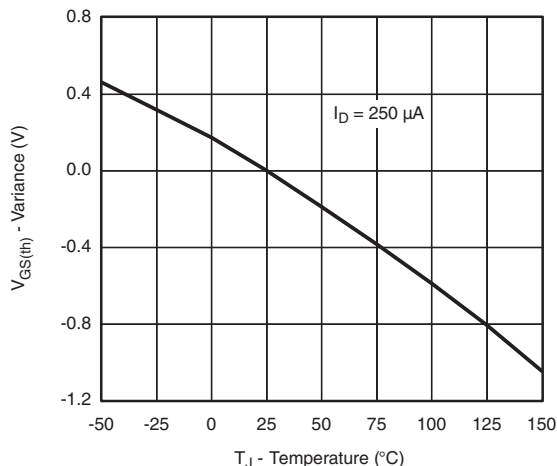
**Capacitance**



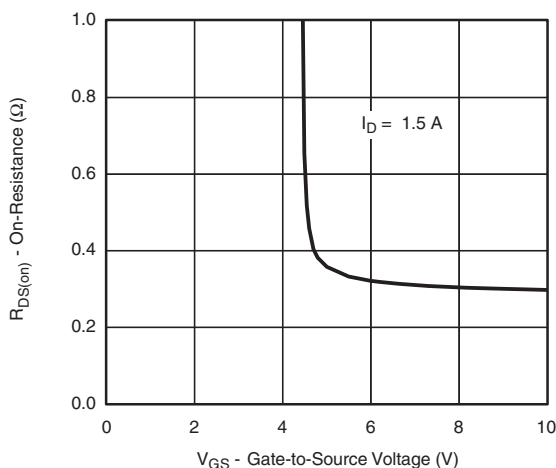
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



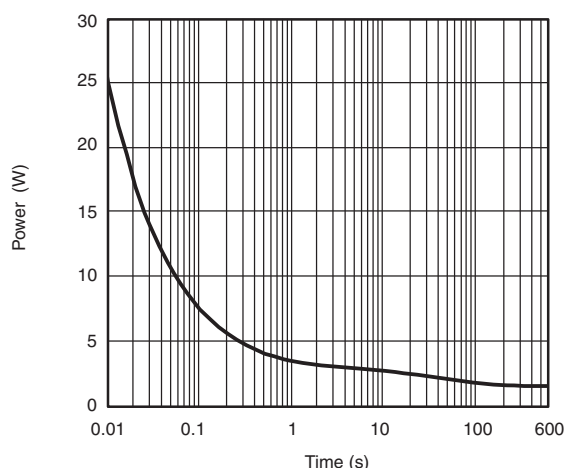
**On-Resistance vs. Junction Temperature**



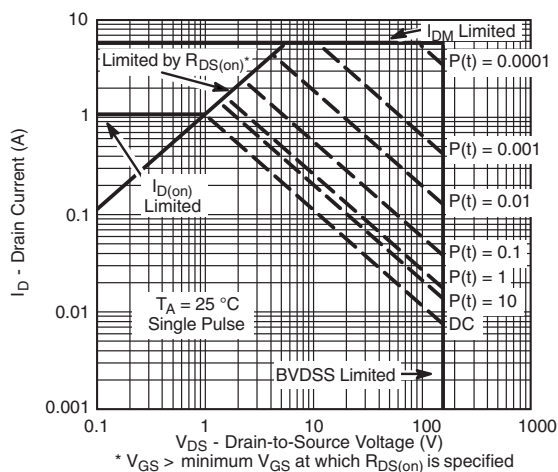
**Threshold Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



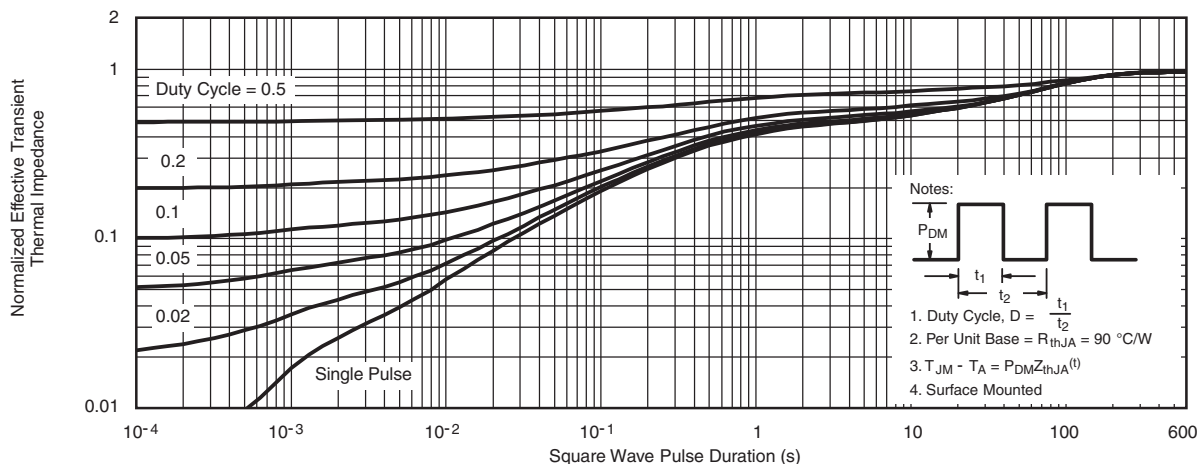
**Single Pulse Power**



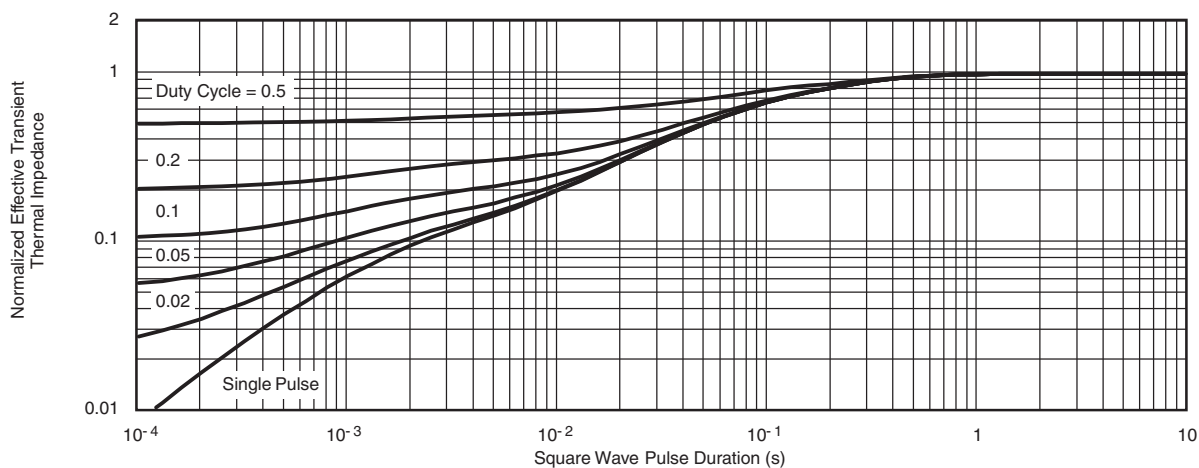
**Safe Operating Area**



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



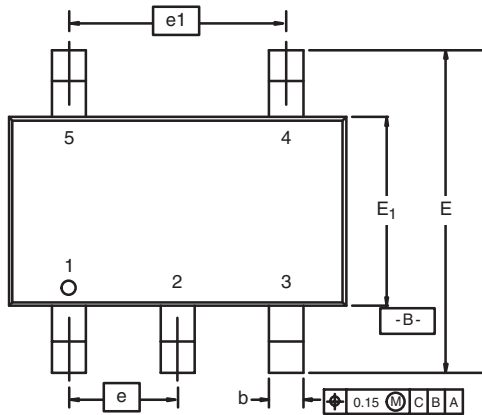
**Normalized Thermal Transient Impedance, Junction-to-Foot**

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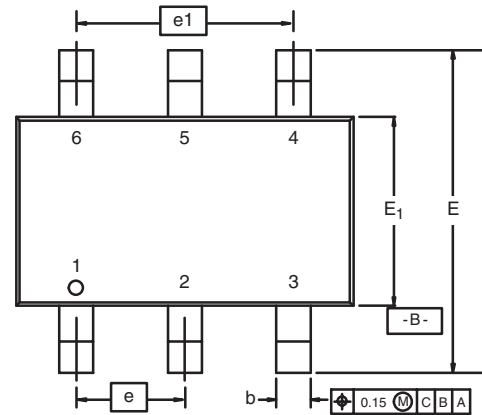


## TSOP: 5/6-LEAD

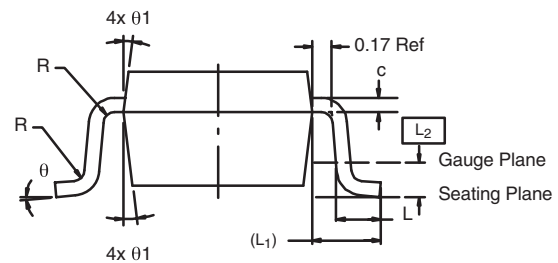
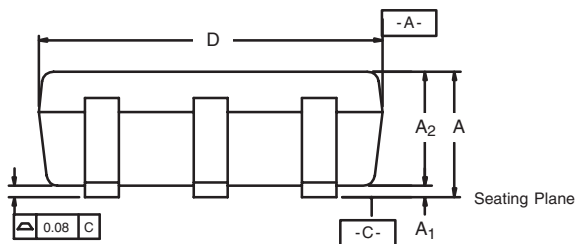
JEDEC Part Number: MO-193C



5-LEAD TSOP

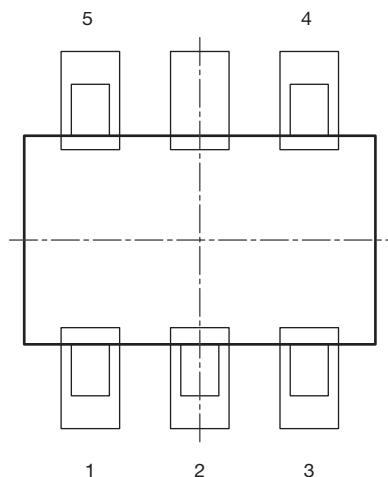


6-LEAD TSOP

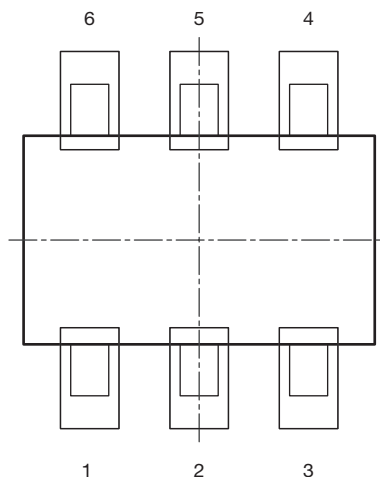


Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ <sub>1</sub>	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

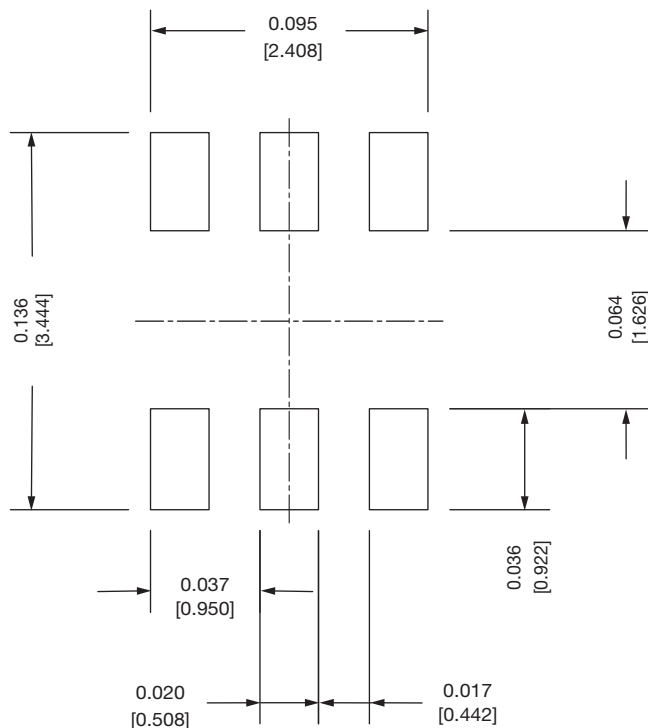
## Recommended Land Pattern For TSOP-5L / TSOP-6L



TSOP 5L



TSOP 6L


**Note**

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022  
DWG: 3010



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